N-Channel 900 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) TYP.	I_D (A)	Q_g (Typ.)
900	4.6 at V_{GS} = 10 V	3	15

FEATURES

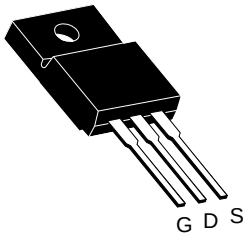
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Gate-Source ESD Protected

RoHS COMPLIANT

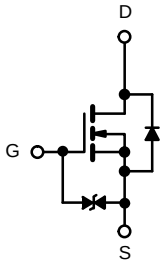
APPLICATIONS

- High efficient switched mode power supplies
- TV Power
- Adapter/charger
- Server Power
- LED Lighting

TO-220 FULLPAK



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	900	V
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	T_C = 25 °C	I_D	3	A
	T_C = 100 °C		1.9	
Pulsed Drain Current (t = 300 µs)		I_{DM}	12	
Avalanche Current		I_{AS}	2.6	
Single Avalanche Energy[a]	L = 0.1 mH	E_{AS}	125	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	90[b]	W
	T_A = 25 °C[c]		5.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	65	°C/W
Junction-to-Case (Drain)	R_{thJC}	5.5	

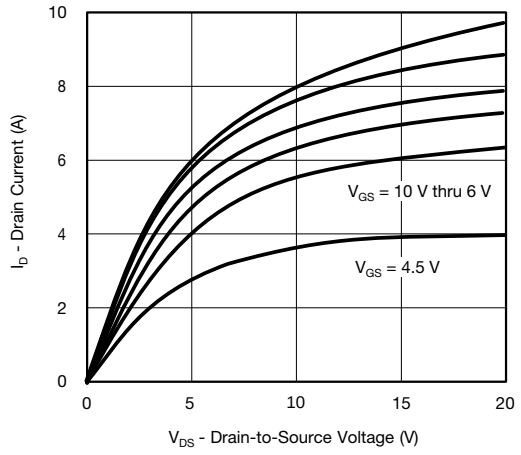
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR-4 material).
d. Base on T_C = 25 °C.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	900			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 30 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 900 V, V_{GS} = 0 V			25	µA
		V_{DS} = 900 V, V_{GS} = 0 V, T_J = 125 °C			100	
		V_{DS} = 900 V, V_{GS} = 0 V, T_J = 150 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 10 V, V_{GS} = 10 V	3			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 2 A,TJ= 25 °C		4.6	5.5	Ω
		V_{GS} = 10 V, I_D = 2 A,TJ= 150 °C		8.8		
Forward Transconductance[a]	g_{fs}	V_{DS} = 20 V, I_D = 2 A		9		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz		561		pF
Output Capacitance	C_{oss}			47		
Reverse Transfer Capacitance	C_{rss}			3.8		
Total Gate Charge[c]	Q_g	V_{DS} = 720 V, V_{GS} = 10 V, I_D = 2 A		15		nC
Gate-Source Charge[c]	Q_{gs}			2.6		
Gate-Drain Charge[c]	Q_{gd}			7.1		
Gate Resistance	R_g	f = 1 MHz		1		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} =720 V, R_L = 9.6 Ω I_D ≅ 2 A, V_{GEN} = 10 V, R_g = 10Ω		8		ns
Rise Time[c]	t_r			12		
Turn-Off Delay Time[c]	$t_{d(off)}$			48		
Fall Time[c]	t_f			15		
Drain-Source Body Diode Ratings and Characteristics[b] T_C = 25 °C						
Continuous Current	I_S				3	A
Pulsed Current	I_{SM}				12	
Forward Voltage[a]	V_{SD}	I_F = 2 A, V_{GS} = 0 V		0.9		V
Reverse Recovery Time	t_{rr}	I_F = 1.5 A, dI/dt = 50 A/µs		626		ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			6		A
Reverse Recovery Charge	Q_{rr}			3		µC

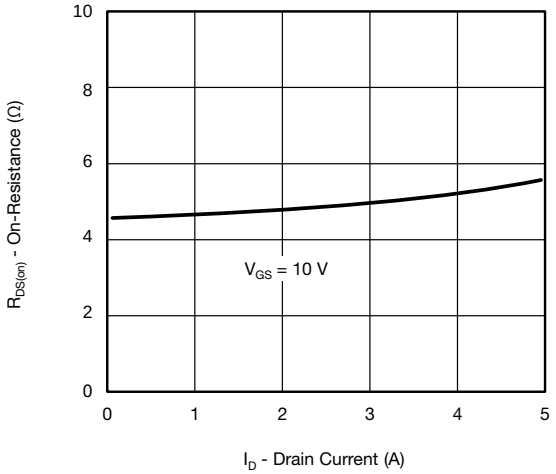
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

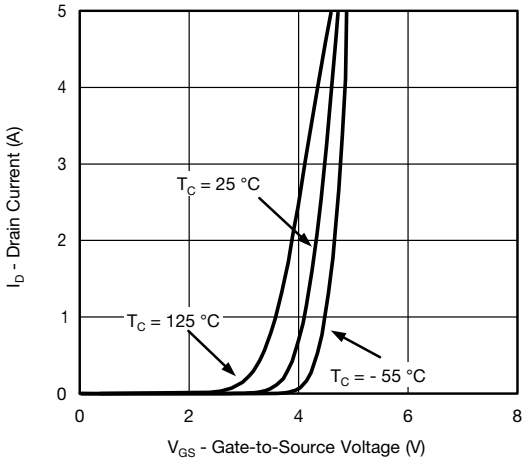
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



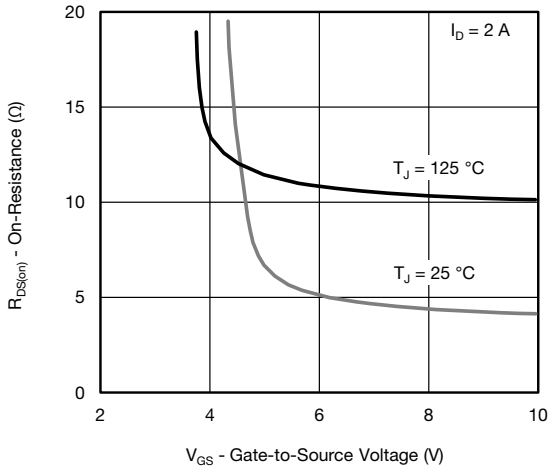
Output Characteristics



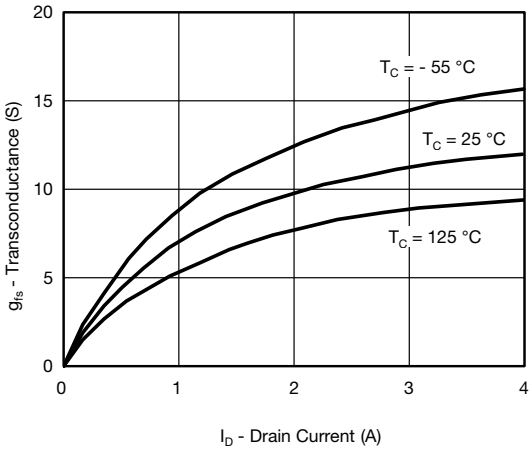
On-Resistance vs. Drain Current



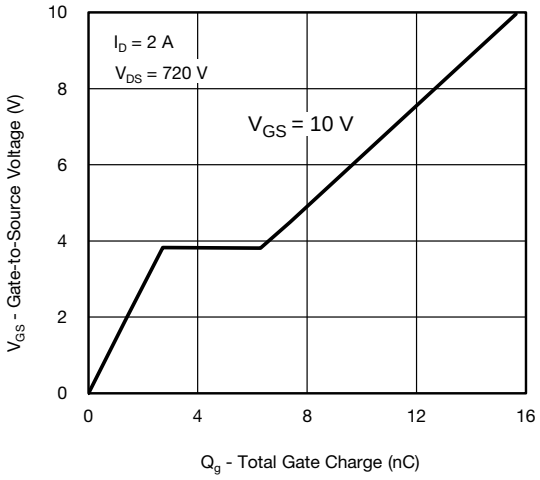
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

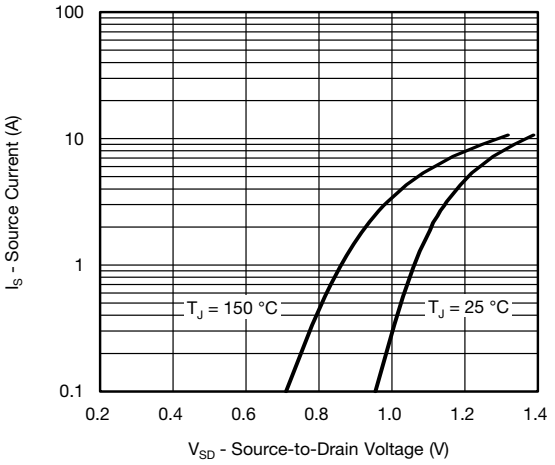


Transconductance

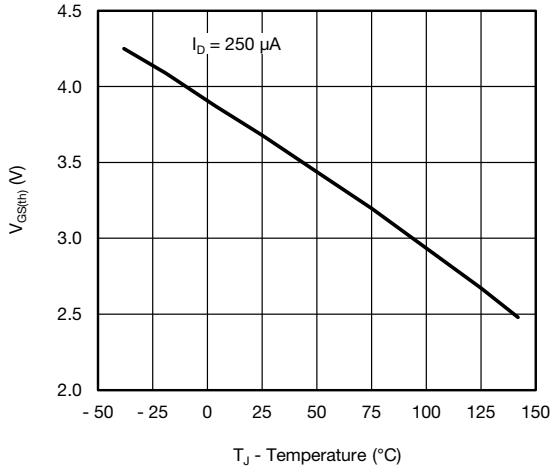


Gate Charge

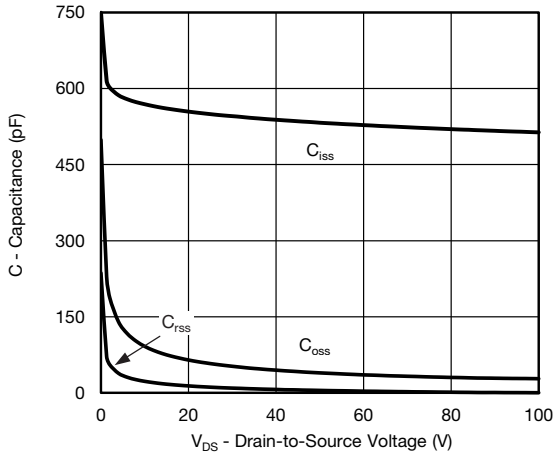
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



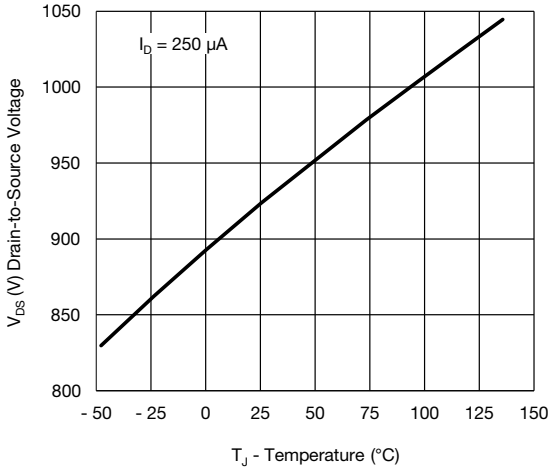
Source-Drain Diode Forward Voltage



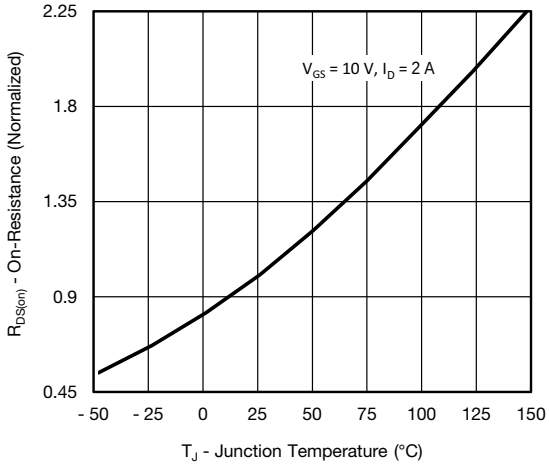
Threshold Voltage



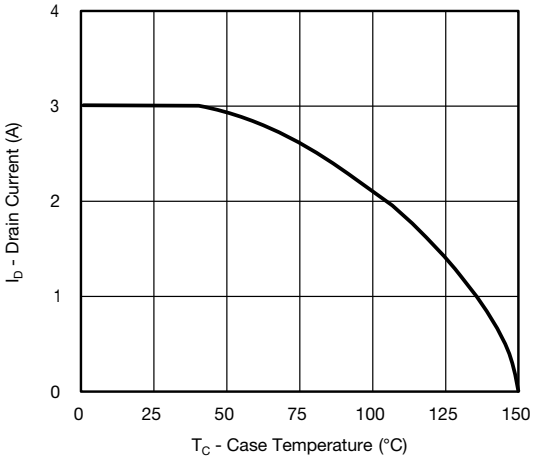
Capacitance



Drain Source Breakdown vs. Junction Temperature

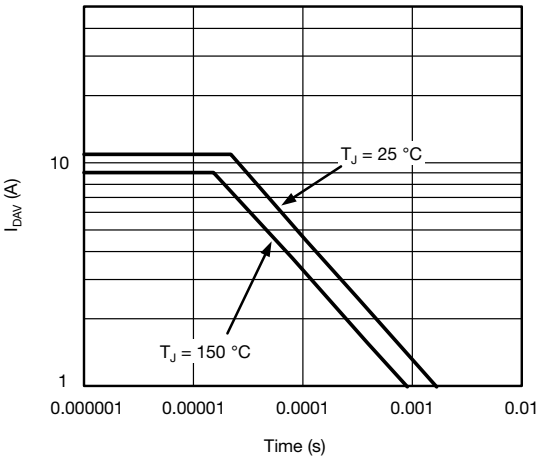


On-Resistance vs. Junction Temperature

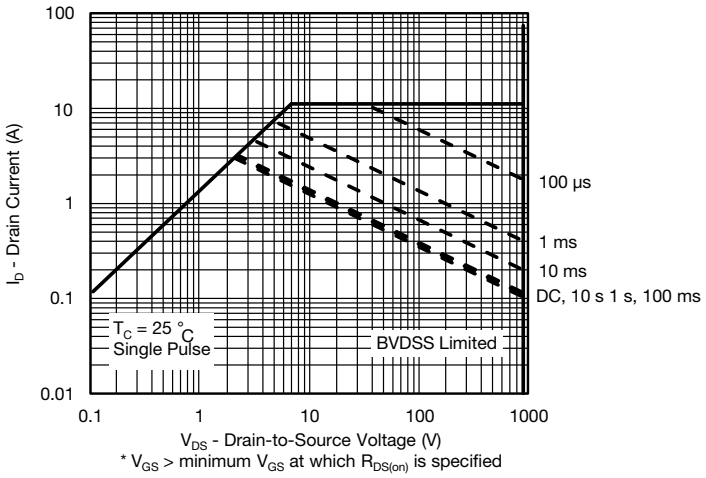


Current Derating

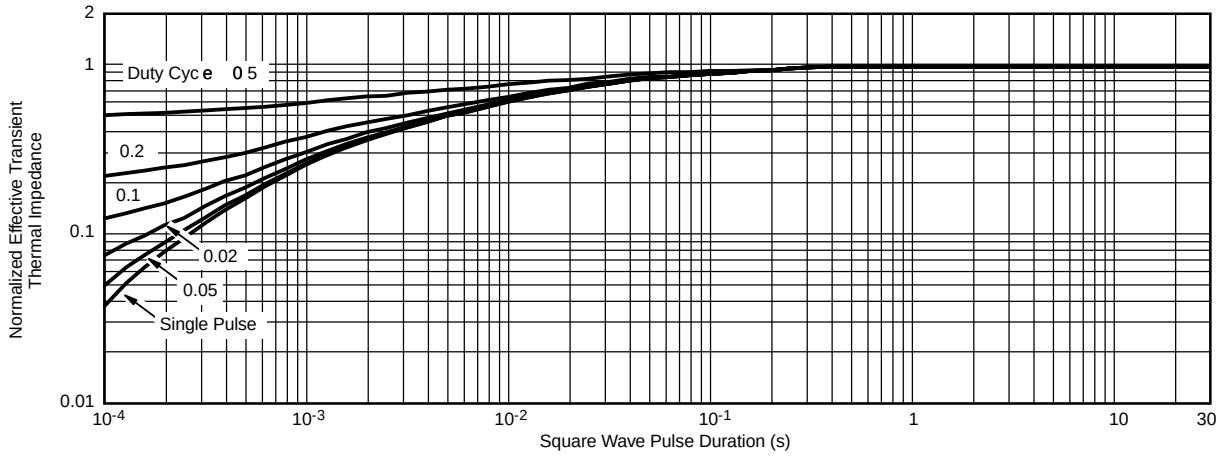
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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